

P-Channel 2.5 V (G-S) MOSFET

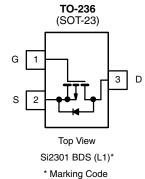
PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A) ^b			
- 20	0.100 at V _{GS} = - 4.5 V	- 2.4			
	0.150 at V _{GS} = - 2.5 V	- 2.0			

FEATURES

- Halogen-free According to IEC 61249-2-21
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



FREE



Ordering Information: Si2301BDS-T1-E3 (Lead (Pb)-free)

Si2301BDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)							
Parameter		Symbol	5 s	Steady State	Unit		
Drain-Source Voltage		V _{DS}	- 20		V		
Gate-Source Voltage		V_{GS}	± 8				
Continuous Dunis Comment /T 150 90\b	T _A = 25 °C	- I _D	- 2.4	- 2.2			
Continuous Drain Current (T _J = 150 °C) ^b	T _A = 70 °C		- 1.9	- 1.8			
Pulsed Drain Current ^a		I _{DM}	- 10		Α		
Continuous Source Current (Diode Conduction) ^b		I _S	- 0.72	- 0.6			
David Dischartisch	T _A = 25 °C	В	0.9	0.7	W		
Power Dissipation ^b	T _A = 70 °C	P _D	0.57	0.45	VV		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient ^b	- R _{thJA}	120	145	°C/W		
Maximum Junction-to-Ambient ^c	TithJA	140	175	C/VV		

- a. Pulse width limited by maximum junction temperature.
- b. Surface mounted on FR4 board, $t \le 5$ s.
- c. Surface mounted on FR4 board.

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.

Si2301BDS

Vishay Siliconix



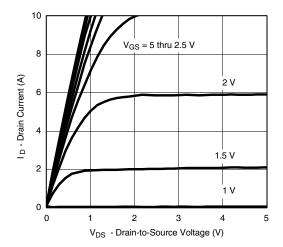
			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V	
Gate Threshold Voltage	V _{GS(th)}				- 0.95	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zava Cata Valtaga Drain Current		V _{DS} = - 20 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 10	μΑ	
		$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 6			А	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -2.5 \text{ V}$	- 3				
	Ь	$V_{GS} = -4.5 \text{ V}, I_D = -2.8 \text{ A}$		0.080	0.100	0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -2 \text{ A}$		0.110	0.150	Ω	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = -5 \text{ V}, I_{D} = -2.8 \text{ A}$		6.5		S	
Diode Forward Voltage	V_{SD}	$I_S = -0.75 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.80	- 1.2	V	
Dynamic ^b			•	•			
Total Gate Charge	Q_g	V 6VV 45V		4.5	10		
Gate-Source Charge	Q _{gs}	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}$ $I_{D} \cong -2.8 \text{ A}$		0.7		nC	
Gate-Drain Charge	Q _{gd}	10 = 2.5 A		1.1			
Gate Resistance	R_g	f = 1 MHz	2	8	16	Ω	
Input Capacitance	C _{iss}			375		pF	
Output Capacitance	C _{oss}	$V_{DS} = -6 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		95			
Reverse Transfer Capacitance	C _{rss}			65			
Switching ^c							
Turn-On Time	t _{d(on)}	V CVP CC		20	30		
Turn-On Time	t _r	$V_{DD} = -6 \text{ V}, R_L = 6 \Omega$ $I_D \cong -1 \text{ A}, V_{GEN} = -4.5 \text{ V}$		40	60	ne	
Turn-Off Time	$t_{d(off)}$			30	45	ns	
ium-on time	t _f	$R_g = 6 \Omega$		20	30]	

- a. Pulse test: pulse width \leq 300 μ s duty cycle \leq 2 %.
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

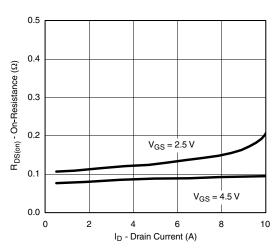
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



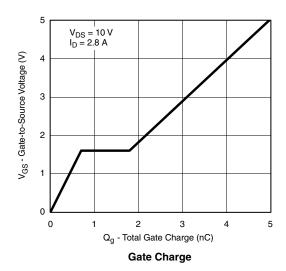
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

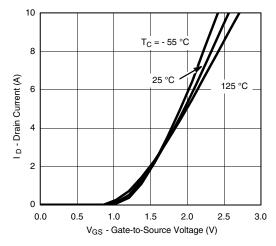


Output Characteristics

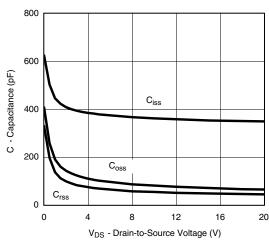


On-Resistance vs. Drain Current

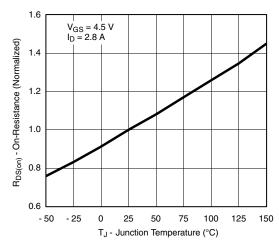




Transfer Characteristics

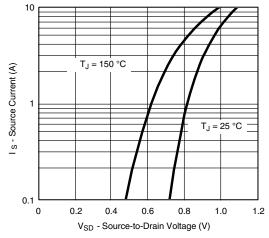


Capacitance

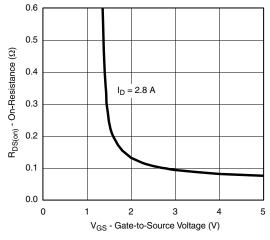


On-Resistance vs. Junction Temperature

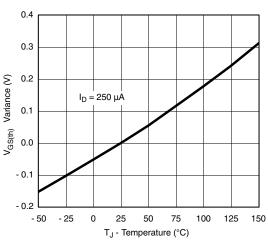
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



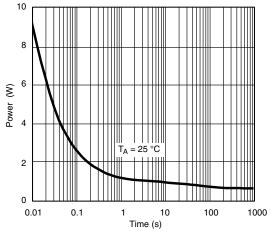
Source-Drain Diode Forward Voltage



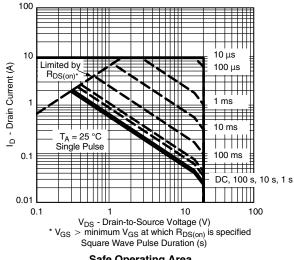
On-Resistance vs. Gate-to-Source Voltage





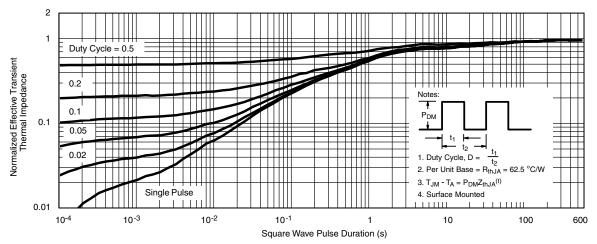


Single Pulse Power



Safe Operating Area

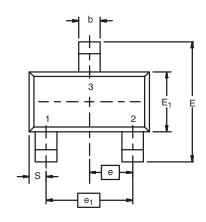
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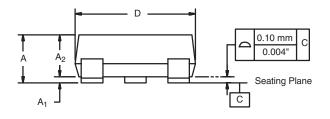


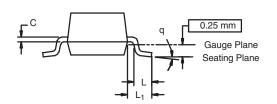
Normalized Thermal Transient Impedance, Junction-to-Ambient

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SOT-23 (TO-236): 3-LEAD







Dim	MILLI	METERS	INCHES			
	Min	Max	Min	Max		
Α	0.89	1.12	0.035	0.044		
A ₁	0.01	0.10	0.0004	0.004		
A ₂	0.88	1.02	0.0346	0.040		
b	0.35	0.50	0.014	0.020		
С	0.085	0.18	0.003	0.007		
D	2.80	3.04	0.110	0.120		
E	2.10	2.64	0.083	0.104		
E ₁	1.20	1.40	0.047	0.055		
е	0.9	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref			
L	0.40	0.60	0.016	0.024		
L ₁	0.64 Ref		0.025 Ref			
S	0.50 Ref		0.020 Ref			
q	3°	8°	3°	8°		
FCN: S-03946-Rev K 09-	lul-01	•				

ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479

Document Number: 71196 www.vishay.com 09-Jul-01



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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